



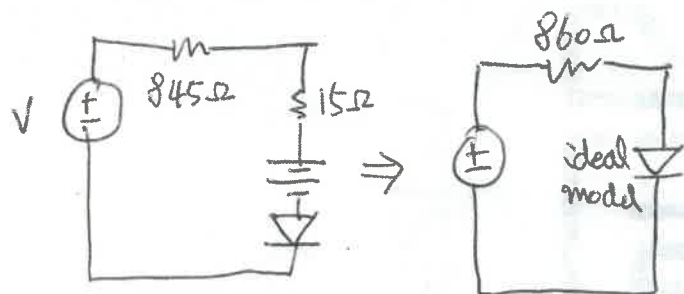
1. a) $X_L = j2\pi fL = j2 \cdot 3.5k \cdot 4m = j280\Omega$ 5점

b) $X_C = -j \frac{1}{2\pi fC} = -j \frac{1}{2 \cdot 3.5k \cdot \frac{1}{3}\mu} = -j100\Omega$ 5점

c) $Z = R + (X_L + X_C) = 100 + j20\Omega$ 5점

d) $Y = G + (B_L + B_C)$
 $= \frac{1}{100} + j(-\frac{1}{120} + \frac{1}{100})$
 $= \frac{1}{100} + j \frac{1}{600} S$ 5점

2. If we apply a piecewise linear model diode to the circuit



a) $I_D = \frac{4.3}{860} = 5mA$ 10점

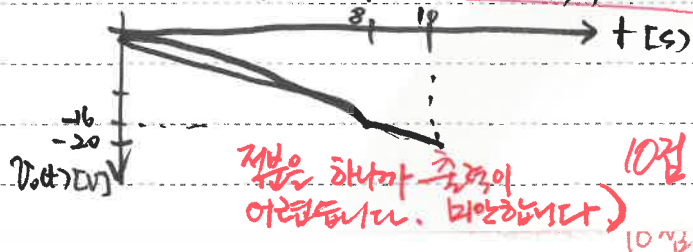
b) $V_D = 0.7 + 15 \cdot 5 \times 10^{-3} = 0.775V$ 10점

3. Integrator (미분기는 생략하고 적분회로라)

a) $i_i + i_f = 0 \therefore \frac{V_i}{R} + C \frac{dV_o(t)}{dt} = 0$

$\therefore V_o(t) = -\frac{1}{Rc} \int v_i(t) dt$
 $= -\frac{1}{2} \int v_i(t) dt$ 10점

b) $v_o(t) = \begin{cases} -\frac{1}{4}t^2, & 0 \leq t \leq 8 \\ -16 - 4(t-8) + (t-8)^2, & 8 \leq t \leq 10 \end{cases}$



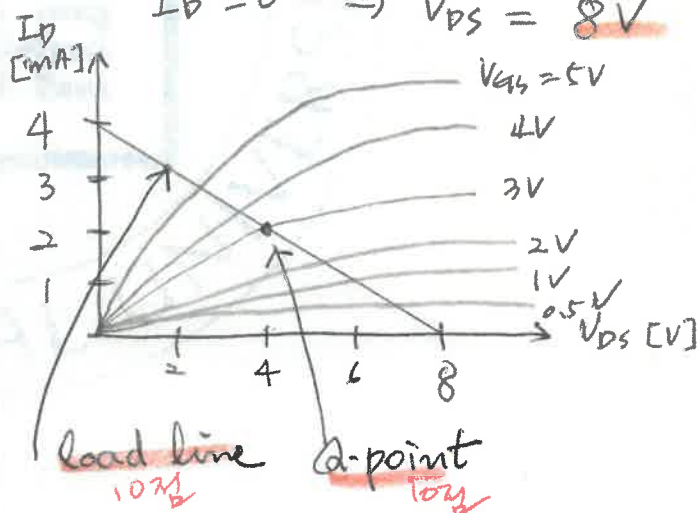
4. a) BJT: Bipolar Binary Junction Transistor 5점

b) MOSFET: Metal Oxide Semiconductor Field Effect Transistor 5점

b) BJT controls the current through it by input current. 5점

FET controls the current through it by the input voltage. 5점

5. a) $V_{DS} = 0 \Rightarrow I_D = 4mA$
 $I_D = 0 \Rightarrow V_{DS} = 8V$



b) $V_{GS} = V_{DD} \frac{R_2}{R_1 + R_2} = 8 \cdot \frac{3k}{3k + 5k} = 3[V]$

\therefore Q-point $\approx (2mA, 4V)$